



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



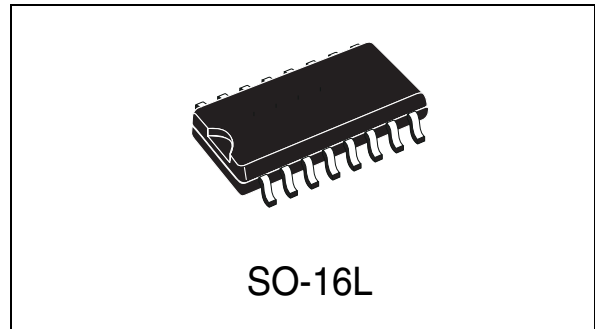
Double channel high-side solid state relay

Features

Type	$R_{DS(on)}$	I_{OUT}	V_{CC}
VND600P-E	35 m Ω	25 A ⁽¹⁾	36 V

1. Per channel with all the output pins connected to the PCB.

- CMOS-compatible input
- Proportional load current sense
- Shorted load protection
- Undervoltage and overvoltage shutdown
- Overvoltage clamp
- Thermal shutdown
- Current limitation
- Protection against loss of ground and loss of V_{CC}
- Very low standby power dissipation
- Reverse battery protected



Description

The VND600P-E is a double chip device designed in STMicroelectronics™ VIPower™ M0-3 technology. The device is intended for driving any type of load with one side connected to ground.

The active V_{CC} pin voltage clamp protects the device against low energy spikes (see ISO7637 transient compatibility table).

Active current limitation combined with thermal shutdown and automatic restart protect the device against overload.

The device integrates an analog current sense output which delivers a current proportional to the load current. The device automatically turns off in the case where the ground pin becomes disconnected.

Table 1. Device summary

Package	Order codes	
	Tube	Tape and reel
SO-16L	VND600P-E	VND600PTR-E

Contents

- 1 Block diagram and pin description 5**

- 2 Electrical specifications 6**
 - 2.1 Absolute maximum ratings 6
 - 2.2 Thermal data 7
 - 2.3 Electrical characteristics 8
 - 2.4 Electrical characteristics curves 14

- 3 Application information 16**
 - 3.1 GND protection network against reverse battery 16
 - 3.1.1 Solution 1: resistor in the ground line (RGND only) 16
 - 3.1.2 Solution 2: diode (DGND) in the ground line 17
 - 3.2 Load dump protection 17
 - 3.3 MCU I/Os protection 17
 - 3.4 Maximum demagnetization energy (VCC = 13.5 V) 18

- 4 Package and PCB thermal data 19**
 - 4.1 SO-16L thermal data 19

- 5 Package and packing information 22**
 - 5.1 ECOPACK® packages 22
 - 5.2 SO-16L packing information 24

- 6 Revision history 25**

List of tables

Table 1.	Device summary	1
Table 2.	Suggested connections for unused and not connected pins	5
Table 3.	Absolute maximum ratings	6
Table 4.	Thermal data (per island)	7
Table 5.	Power	8
Table 6.	Switching ($V_{CC} = 13\text{ V}$)	8
Table 7.	V_{CC} output diode.	8
Table 8.	Logic inputs.	9
Table 9.	Current sense ($9\text{ V} \leq V_{CC} \leq 16\text{ V}$)	9
Table 10.	Protections	10
Table 11.	Truth table.	10
Table 12.	Electrical transient requirements	11
Table 13.	Thermal parameters	21
Table 14.	SO-16L mechanical data	23
Table 15.	Document revision history	25

List of figures

Figure 1.	Block diagram	5
Figure 2.	Configuration diagram (top view)	5
Figure 3.	Current and voltage conventions ⁽¹⁾	6
Figure 4.	Switching characteristics	11
Figure 5.	I_{OUT}/I_{SENSE} versus I_{OUT}	12
Figure 6.	Waveforms	13
Figure 7.	Off-state output current.	14
Figure 8.	High-level input current.	14
Figure 9.	Input clamp voltage.	14
Figure 10.	Turn-on voltage slope.	14
Figure 11.	Overshoot shutdown	14
Figure 12.	Turn-off voltage slope.	14
Figure 13.	I_{LIM} vs T_{case}	15
Figure 14.	On-state resistance vs V_{CC}	15
Figure 15.	Input high-level	15
Figure 16.	Input hysteresis voltage	15
Figure 17.	On-state resistance vs T_{case}	15
Figure 18.	Input low-level.	15
Figure 19.	Application schematic.	16
Figure 20.	Maximum turn-off current versus inductance ⁽¹⁾	18
Figure 21.	SO-16L PC board ⁽¹⁾	19
Figure 22.	$R_{thj-amb}$ vs PCB copper area in open box free air condition	19
Figure 23.	Thermal impedance junction ambient single pulse	20
Figure 24.	Thermal fitting model of a quad channel HSD in SO-16L.	20
Figure 25.	SO-16L package dimensions	22
Figure 26.	SO-16L tube shipment (no suffix)	24
Figure 27.	SO-16L tape and reel shipment (suffix "TR")	24

1 Block diagram and pin description

Figure 1. Block diagram

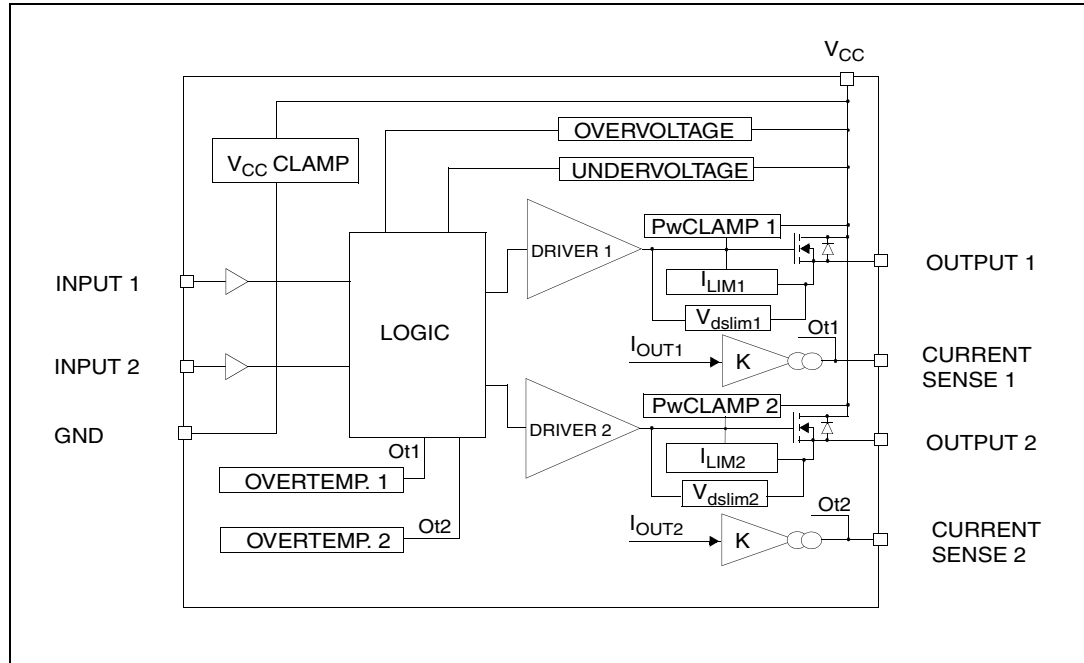


Figure 2. Configuration diagram (top view)

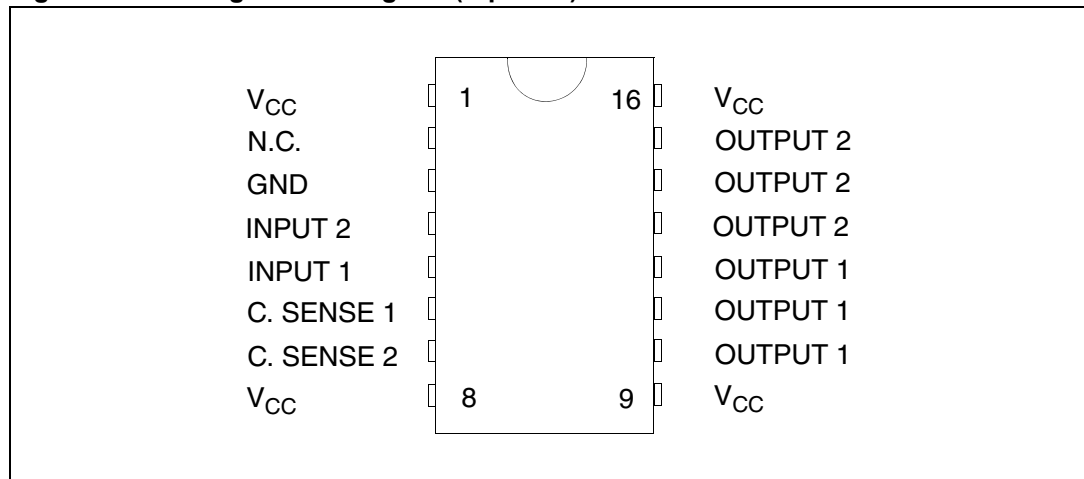
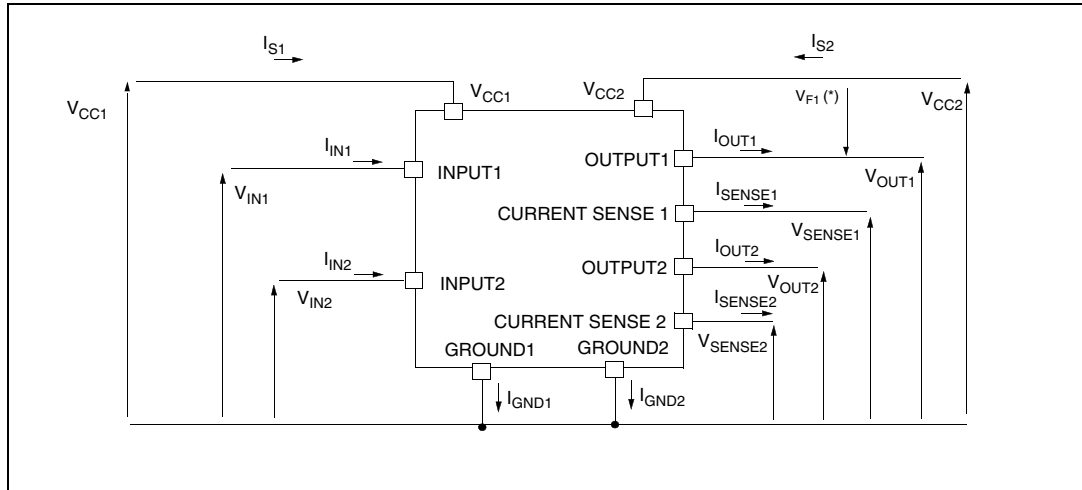


Table 2. Suggested connections for unused and not connected pins

Connection / pin	Current sense	N.C.	Output	Input
Floating		X	X	X
To ground	Through 1 KΩ resistor	X		Through 10 KΩ resistor

2 Electrical specifications

Figure 3. Current and voltage conventions⁽¹⁾



1. $V_{Fn} = V_{CCn} - V_{OUTn}$ during reverse battery condition.

2.1 Absolute maximum ratings

Stressing the device above the rating listed in the “Absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to Absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics sure program and other relevant quality document.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	DC supply voltage	41	V
$-V_{CC}$	Reverse DC supply voltage	- 0.3	V
$-I_{gnd}$	DC reverse ground pin current	- 200	mA
I_{OUT}	DC output current	Internally limited	A
$-I_{OUT}$	Reverse DC output current	- 21	A
I_{IN}	DC input current	+/- 10	mA
$V_{CSSENSE}$	Current Sense maximum voltage	- 3 + 15	V V
V_{ESD}	Electrostatic discharge (human body model: R = 1.5 K Ω ; C = 100 pF)		
	- INPUT	4000	V
	- CURRENT SENSE	2000	V
	- OUTPUT	5000	V
	- V_{CC}	5000	V

Table 3. Absolute maximum ratings (continued)

Symbol	Parameter	Value	Unit
E_{MAX}	Maximum switching energy ($L = 0.12 \text{ mH}$; $R_L = 0 \text{ } \Omega$; $V_{bat} = 13.5 \text{ V}$; $T_{jstart} = 150 \text{ } ^\circ\text{C}$; $I_L = 40 \text{ A}$)	136	mJ
P_{tot}	Power dissipation $T_C \leq 25 \text{ } ^\circ\text{C}$	8.3	W
T_j	Junction operating temperature	Internally limited	$^\circ\text{C}$
T_C	Case operating temperature	- 40 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$

2.2 Thermal data

Table 4. Thermal data (per island)

Symbol	Parameter	Value		Unit
$R_{thj-lead}$	Thermal resistance junction-lead	15		$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	65 ⁽¹⁾	48 ⁽²⁾	$^\circ\text{C}/\text{W}$

1. When mounted on a standard single-sided FR-4 board with 0.5cm^2 of Cu (at least $35 \text{ } \mu\text{m}$ thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.
2. When mounted on a standard single-sided FR-4 board with 6cm^2 of Cu (at least $35 \text{ } \mu\text{m}$ thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.

2.3 Electrical characteristics

Values specified in this section are for $8\text{ V} < V_{CC} < 36\text{ V}$; $-40\text{ °C} < T_j < 150\text{ °C}$, unless otherwise stated.

Table 5. Power

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC}	Operating supply voltage		5.5	13	36	V
V_{USD}	Undervoltage shutdown		3	4	5.5	V
$V_{OV}^{(1)}$	Overvoltage shutdown		36			V
R_{ON}	On-state resistance	$I_{OUT} = 5\text{ A}$; $T_j = 25\text{ °C}$;			35	m Ω
		$I_{OUT} = 5\text{ A}$; $T_j = 150\text{ °C}$;			70	m Ω
		$I_{OUT} = 3\text{ A}$; $V_{CC} = 6\text{ V}$			120	m Ω
$V_{CLAMP}^{(1)}$	Clamp voltage	$I_{CC} = 20\text{ mA}$	41	48	55	V
I_S	Supply current	Off-state; $V_{CC} = 13\text{ V}$; $V_{IN} = V_{OUT} = 0\text{ V}$		12	40	μA
		Off-state; $V_{CC} = 13\text{ V}$; $V_{IN} = V_{OUT} = 0\text{ V}$; $T_j = 25\text{ °C}$		12	25	μA
		On-state; $V_{CC} = 13\text{ V}$; $V_{IN} = 5\text{ V}$; $I_{OUT} = 0\text{ A}$; $R_{SENSE} = 3.9\text{ k}\Omega$			6	mA
$I_{L(off1)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$	0		50	μA
$I_{L(off2)}$	Off-state output current	$V_{IN} = 0\text{ V}$; $V_{OUT} = 3.5\text{ V}$	-75		0	μA
$I_{L(off3)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$; $V_{CC} = 13\text{ V}$; $T_j = 125\text{ °C}$			5	μA
$I_{L(off4)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$; $V_{CC} = 13\text{ V}$; $T_j = 25\text{ °C}$			3	μA

1. V_{CLAMP} and V_{OV} are correlated. Typical difference is 5 V.

Table 6. Switching ($V_{CC} = 13\text{ V}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$R_L = 2.6\ \Omega$ (see Figure 4)		30		μs
$t_{d(off)}$	Turn-off delay time	$R_L = 2.6\ \Omega$ (see Figure 4)		30		μs
$dV_{OUT}/dt_{(on)}$	Turn-on voltage slope	$R_L = 2.6\ \Omega$ (see Figure 4)		See Figure 10		V/ μs
$dV_{OUT}/dt_{(off)}$	Turn-off voltage slope	$R_L = 2.6\ \Omega$ (see Figure 4)		See Figure 12		V/ μs

Table 7. V_{CC} output diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on voltage	$-I_{OUT} = 2.3\text{ A}$; $T_j = 150\text{ °C}$	—	—	0.6	V

Table 8. Logic inputs

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IL}	Input low-level voltage				1.25	V
I_{IL}	Low-level input current	$V_{IN} = 1.25\text{ V}$	1			μA
V_{IH}	Input high-level voltage		3.25			V
I_{IH}	High-level input current	$V_{IN} = 3.25\text{ V}$			10	μA
$V_{I(hyst)}$	Input hysteresis voltage		0.5			V
V_{ICL}	Input clamp voltage	$I_{IN} = 1\text{ mA}$	6	6.8	8	V
		$I_{IN} = -1\text{ mA}$		-0.7		V

Table 9. Current sense ($9\text{ V} \leq V_{CC} \leq 16\text{ V}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
K_1	I_{OUT}/I_{SENSE}	$I_{OUT} = 0.5\text{ A}; V_{SENSE} = 0.5\text{ V};$ $T_j = -40\text{ }^\circ\text{C} \dots 150\text{ }^\circ\text{C}$	3300	4400	6000	
dK_1/K_1	Current sense ratio drift	$I_{OUT} = 0.5\text{ A}; V_{SENSE} = 0.5\text{ V};$ $T_j = -40\text{ }^\circ\text{C} \dots 150\text{ }^\circ\text{C}$	- 10		+ 10	%
K_2	I_{OUT}/I_{SENSE}	$I_{OUT} = 5\text{ A}; V_{SENSE} = 4\text{ V};$ $T_j = -40\text{ }^\circ\text{C}$ $T_j = 25\text{ }^\circ\text{C} \dots 150\text{ }^\circ\text{C}$	4200 4400	4900 4900	6000 5750	
dK_2/K_2	Current sense ratio drift	$I_{OUT} = 5\text{ A}; V_{SENSE} = 4\text{ V};$ $T_j = -40\text{ }^\circ\text{C} \dots 150\text{ }^\circ\text{C}$	- 6		+ 6	%
K_3	I_{OUT}/I_{SENSE}	$I_{OUT} = 15\text{ A}; V_{SENSE} = 4\text{ V};$ $T_j = -40\text{ }^\circ\text{C}$ $T_j = 25\text{ }^\circ\text{C} \dots 150\text{ }^\circ\text{C}$	4200 4400	4900 4900	5500 5250	
dK_3/K_3	Current sense ratio drift	$I_{OUT} = 15\text{ A}; V_{SENSE} = 4\text{ V};$ $T_j = -40\text{ }^\circ\text{C} \dots 150\text{ }^\circ\text{C}$	- 6		+ 6	%
V_{SENSE}	Max analog sense output voltage	$V_{CC} = 5.5\text{ V}; I_{OUT} = 2.5\text{ A};$ $R_{SENSE} = 10\text{ k}\Omega$	2			V
		$V_{CC} > 8\text{ V}; I_{OUT} = 5\text{ A};$ $R_{SENSE} = 10\text{ k}\Omega$	4			V
V_{SENSEH}	Sense voltage in overtemperature condition	$V_{CC} = 13\text{ V}; R_{SENSE} = 3.9\text{ k}\Omega$		5.5		V
$R_{VSENSEH}$	Analog sense output impedance in overtemperature condition	$V_{CC} = 13\text{ V}; T_j > T_{TSD};$ output open		400		Ω
t_{DSENSE}	Current sense delay response	To 90 % $I_{SENSE}^{(1)}$			500	μs

1. Current sense signal delay after positive input slope.

Table 10. Protections⁽¹⁾

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
T _{TSD}	Shutdown temperature		150	175	200	°C
T _R	Reset temperature		135			°C
T _{hyst}	Thermal hysteresis		7	15		°C
I _{lim}	Current limitation	V _{CC} = 13 V	25	40	70	A
		5 V < V _{CC} < 36 V			70	A
V _{demag}	Turn-off output clamp voltage	I _{OUT} = 2 A; V _{IN} = 0 V; L = 6 mH	V _{CC} - 41	V _{CC} - 48	V _{CC} - 55	V
V _{ON}	Output voltage drop limitation	I _{OUT} = 0.5 A; T _j = -40 °C...150 °C		50		mV

1. To ensure long term reliability under heavy overload or short circuit conditions, protection and related diagnostic signals must be used together with a proper software strategy. If the device operates under abnormal conditions this software must limit the duration and number of activation cycles.

Table 11. Truth table

Conditions	Input	Output	Sense
Normal operation	L	L	0
	H	H	Nominal
Overtemperature	L	L	0
	H	L	V _{SENSEH}
Undervoltage	L	L	0
	H	L	0
Overvoltage	L	L	0
	H	L	0
Short circuit to GND	L	L	0
	H	L	(T _j < T _{TSD}) 0 (T _j > T _{TSD}) V _{SENSEH}
Short circuit to V _{CC}	L	H	0
	H	H	< Nominal
Negative output voltage clamp	L	L	0

Table 12. Electrical transient requirements

ISO T/R 7637/1 Test pulse	Test level				Delays and impedance
	I	II	III	IV	
1	- 25 V ⁽¹⁾	- 50 V ⁽¹⁾	- 75 V ⁽¹⁾	- 100 V ⁽¹⁾	2 ms, 10 Ω
2	+ 25 V ⁽¹⁾	+ 50 V ⁽¹⁾	+ 75 V ⁽¹⁾	+ 100 V ⁽¹⁾	0.2 ms, 10 Ω
3a	- 25 V ⁽¹⁾	- 50 V ⁽¹⁾	- 100 V ⁽¹⁾	- 150 V ⁽¹⁾	0.1 μs, 50 Ω
3b	+ 25 V ⁽¹⁾	+ 50 V ⁽¹⁾	+ 75 V ⁽¹⁾	+ 100 V ⁽¹⁾	0.1 μs, 50 Ω
4	- 4 V ⁽¹⁾	- 5 V ⁽¹⁾	- 6 V ⁽¹⁾	- 7 V ⁽¹⁾	100 ms, 0.01 Ω
5	+ 26.5 V ⁽¹⁾	+ 46.5 V ⁽²⁾	+ 66.5 V ⁽²⁾	+ 86.5 V ⁽²⁾	400 ms, 2 Ω

1. All functions of the device are performed as designed after exposure to disturbance.
2. One or more functions of the device is not performed as designed after exposure and cannot be returned to proper operation without replacing the device.

Figure 4. Switching characteristics

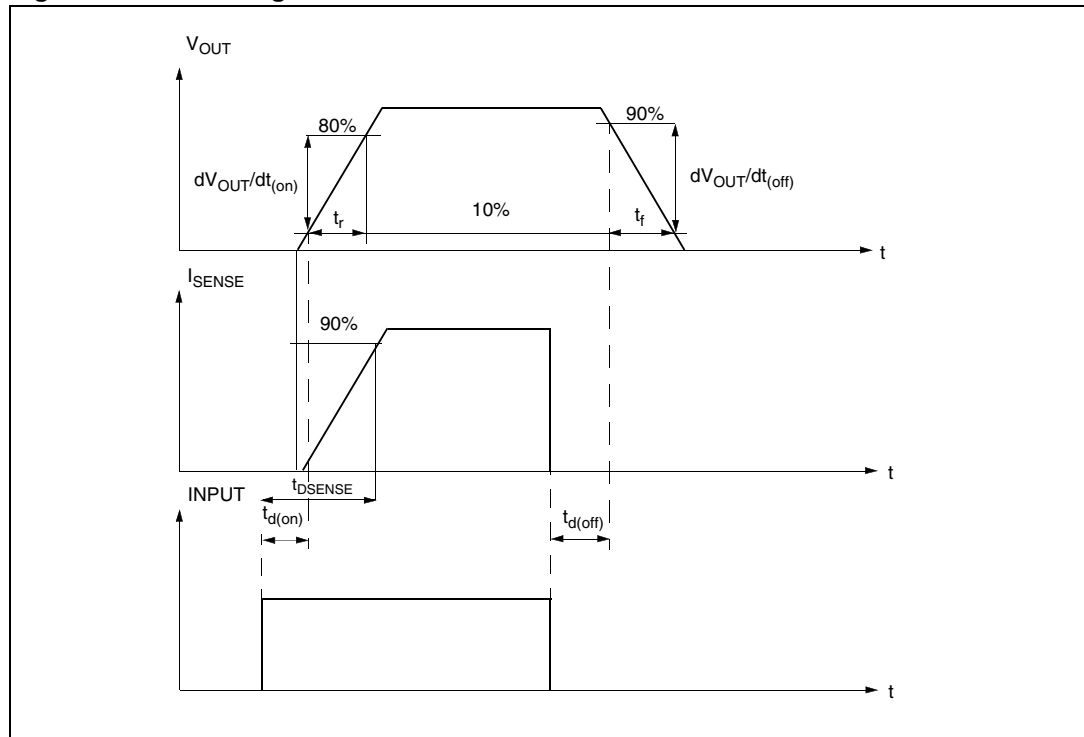


Figure 5. I_{OUT}/I_{SENSE} versus I_{OUT}

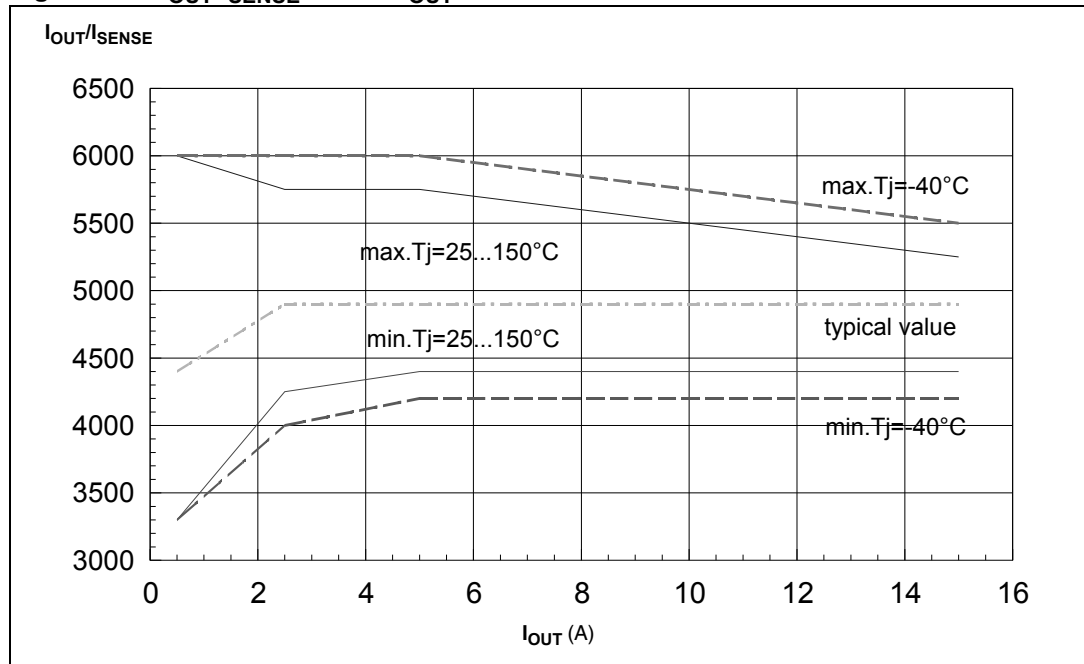
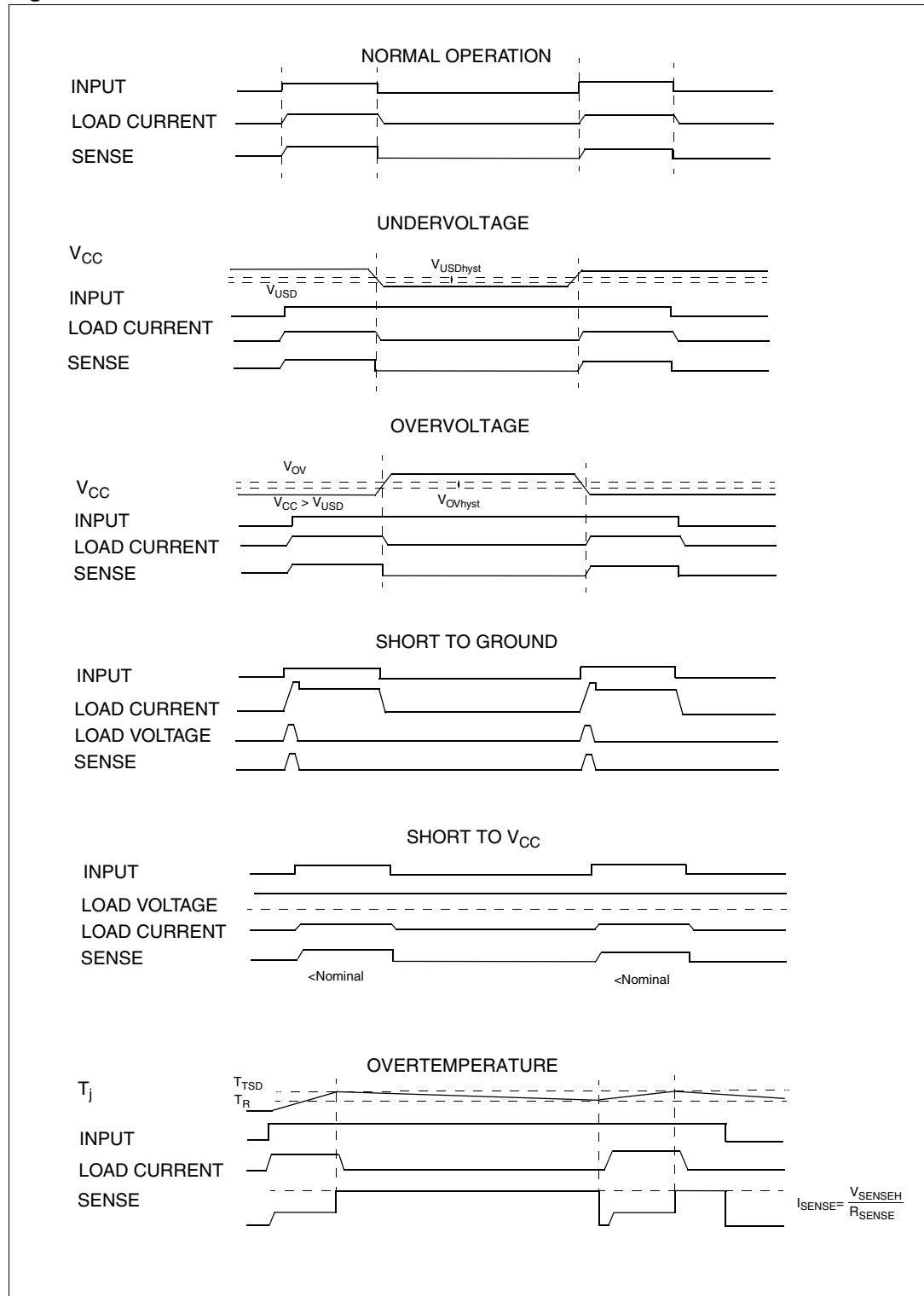


Figure 6. Waveforms



2.4 Electrical characteristics curves

Figure 7. Off-state output current

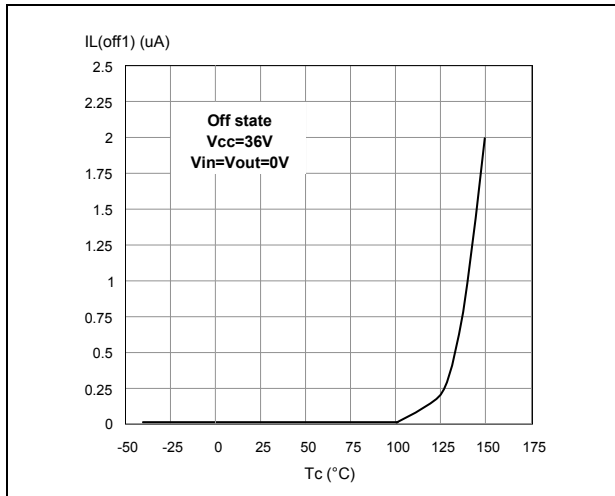


Figure 8. High-level input current

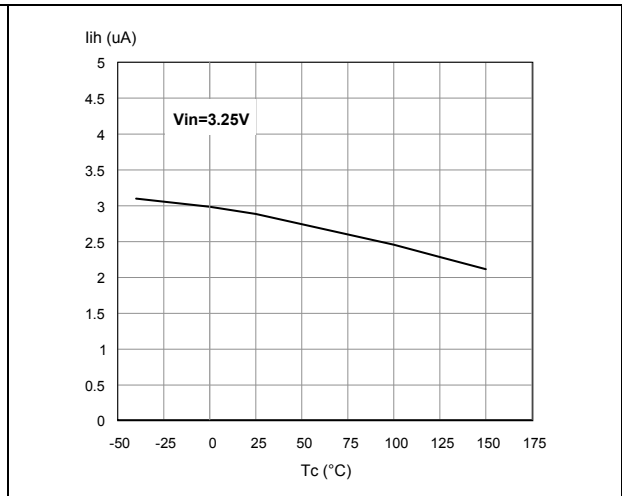


Figure 9. Input clamp voltage

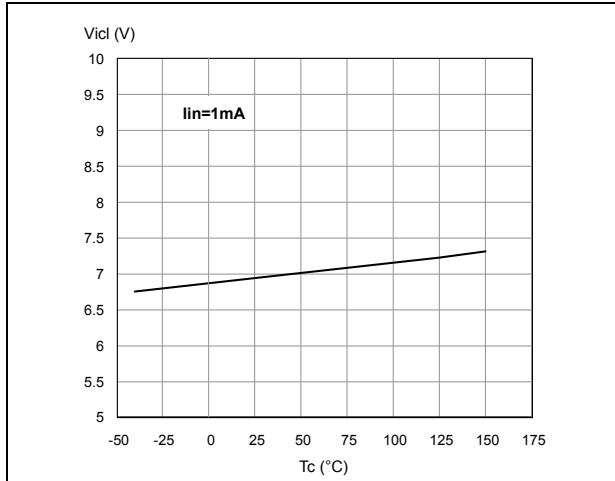


Figure 10. Turn-on voltage slope

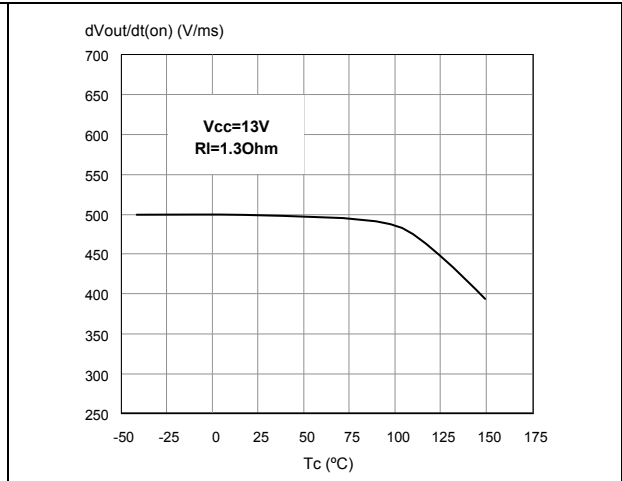


Figure 11. Overvoltage shutdown

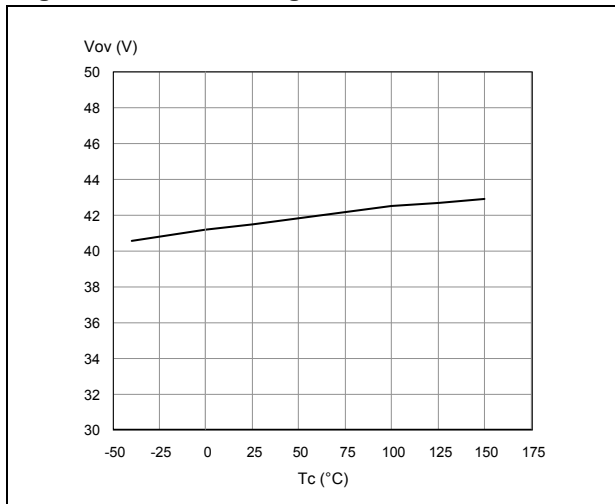


Figure 12. Turn-off voltage slope

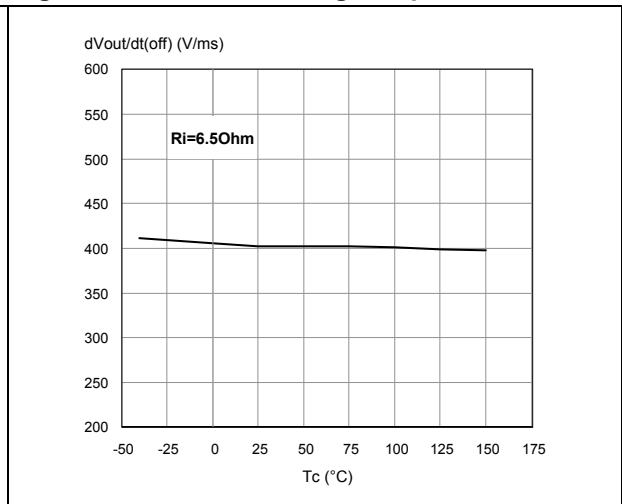


Figure 13. I_{LIM} vs T_{case}

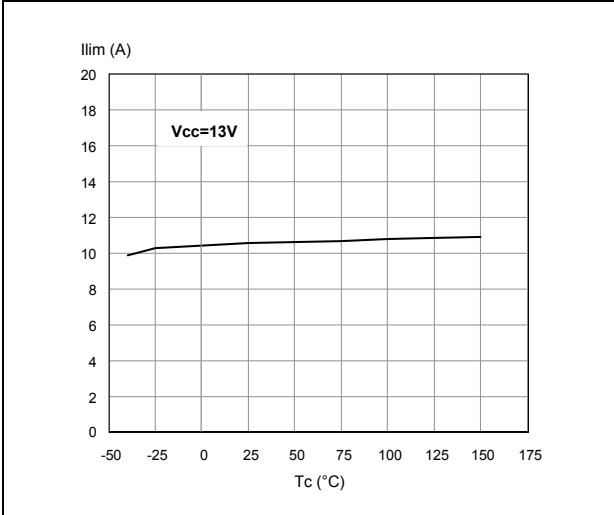


Figure 14. On-state resistance vs V_{CC}

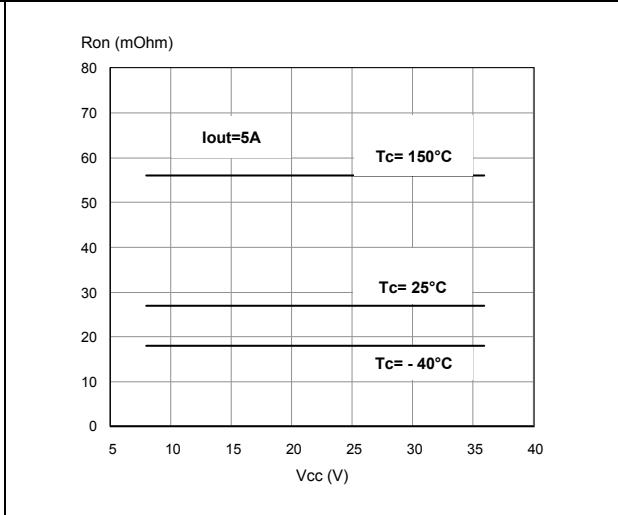


Figure 15. Input high-level

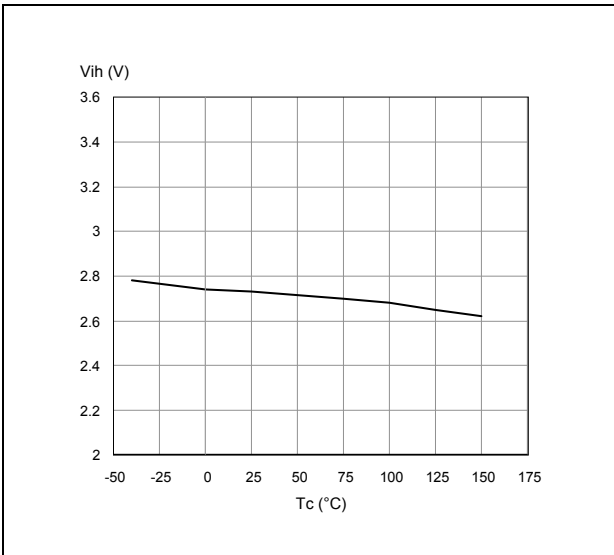


Figure 16. Input hysteresis voltage

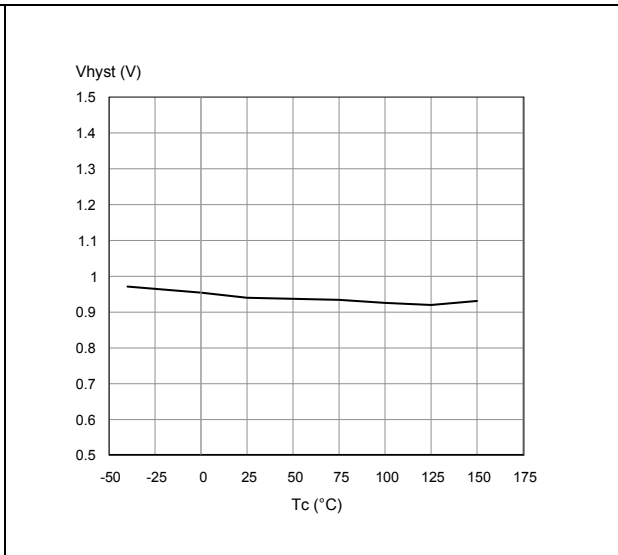


Figure 17. On-state resistance vs T_{case}

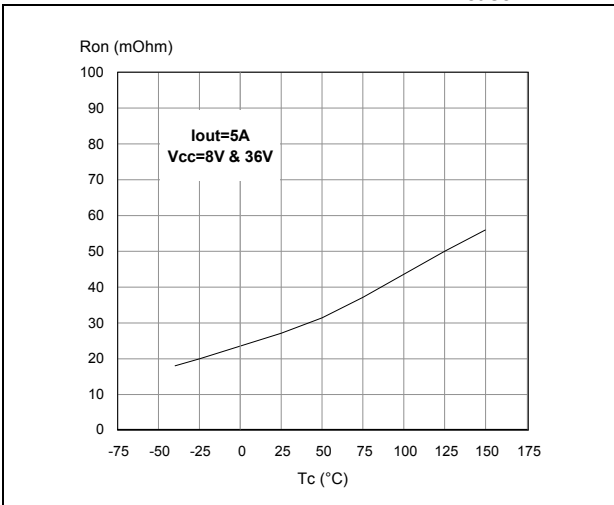
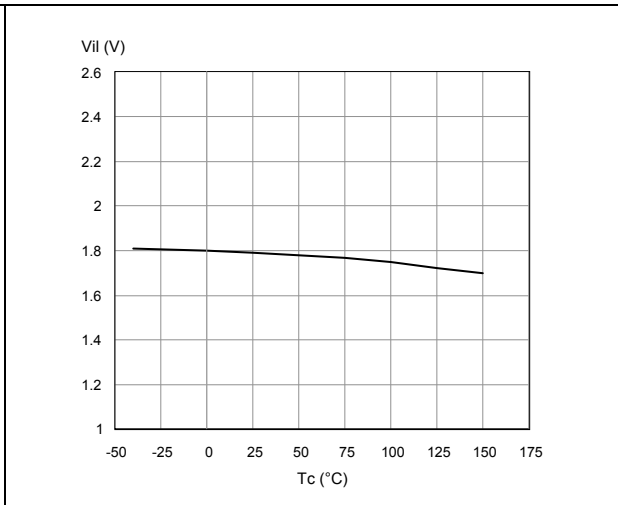
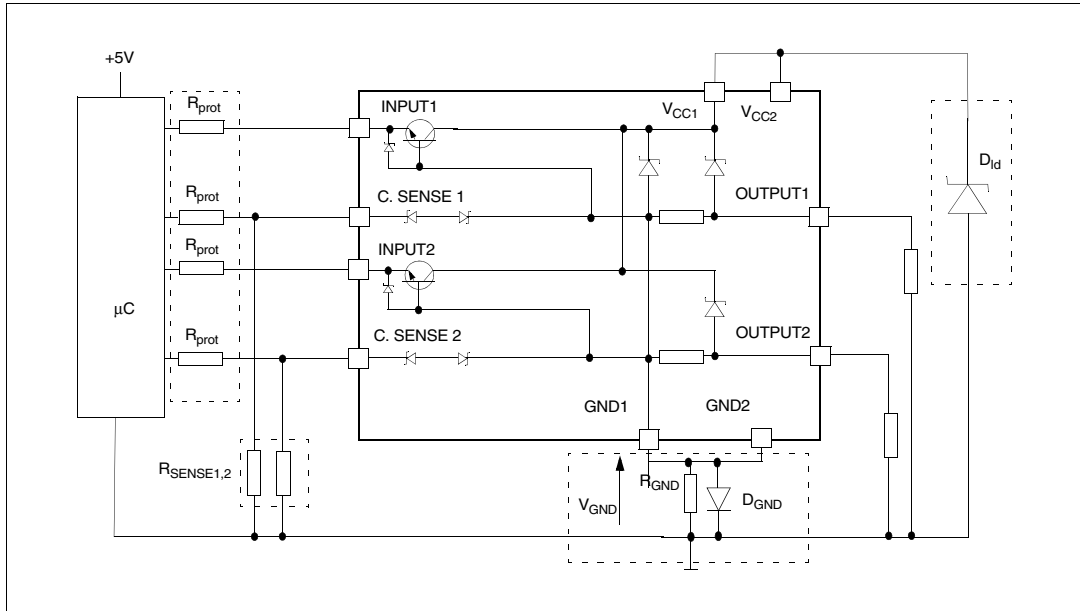


Figure 18. Input low-level



3 Application information

Figure 19. Application schematic



3.1 GND protection network against reverse battery

3.1.1 Solution 1: resistor in the ground line (R_{GND} only)

This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

1. $R_{GND} \leq 600 \text{ mV} / (I_{S(on)max})$
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power Dissipation in R_{GND} (when $V_{CC} < 0$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not shared by the device ground then the R_{GND} produces a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift varies depending on how many devices are ON in the case of several high-side drivers sharing the same R_{GND}.

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then ST suggests to utilize Solution 2 (see below).

3.1.2 Solution 2: diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 1 \text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network produces a shift ($\approx 600 \text{ mV}$) in the input threshold and in the status output values if the microprocessor ground is not common to the device ground. This shift not varies if more than one HSD shares the same diode/resistor network.

Series resistor in INPUT and STATUS lines are also required to prevent that, during battery voltage transient, the current exceeds the absolute maximum rating.

Safest configuration for unused INPUT and STATUS pin is to leave them unconnected.

3.2 Load dump protection

D_{ld} is necessary (Voltage Transient Suppressor) if the load dump peak voltage exceeds the V_{CC} max DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than the ones shown in the ISO 7637-2: 2004(E) table.

3.3 MCU I/Os protection

If a ground protection network is used and negative transient are present on the V_{CC} line, the control pins are pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the microcontroller I/O pins to latch-up.

The value of these resistors is a compromise between the leakage current of microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os.

$$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

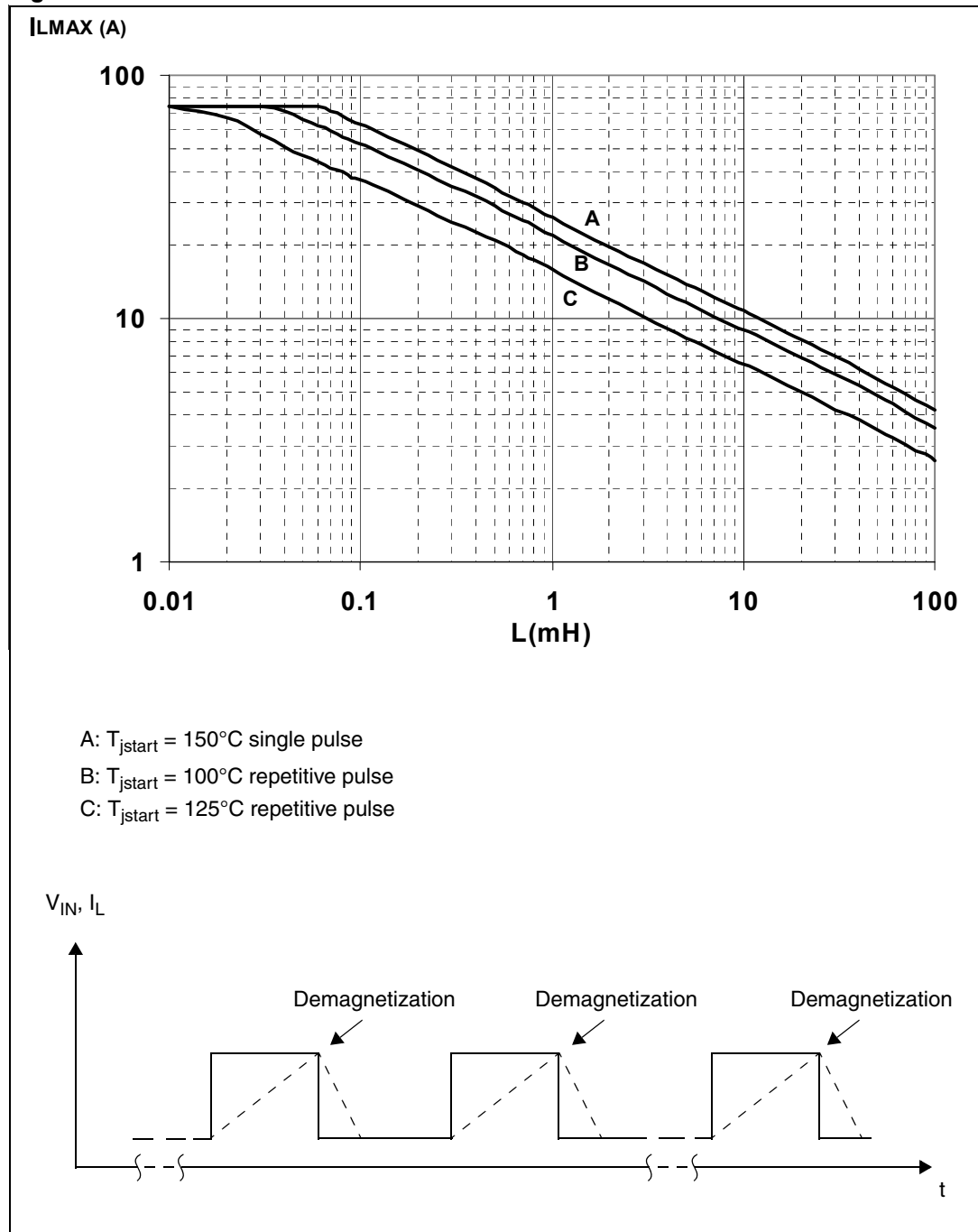
For $V_{CCpeak} = -100 \text{ V}$ and $I_{latchup} \geq 20 \text{ mA}$; $V_{OH\mu C} \geq 4.5 \text{ V}$

$$5 \text{ k}\Omega \leq R_{prot} \leq 65 \text{ k}\Omega$$

Recommended values: $R_{prot} = 10 \text{ k}\Omega$.

3.4 Maximum demagnetization energy ($V_{CC} = 13.5\text{ V}$)

Figure 20. Maximum turn-off current versus inductance⁽¹⁾

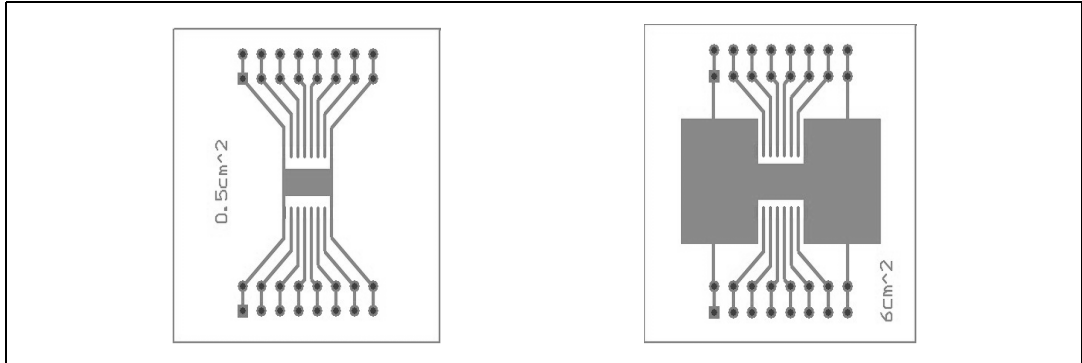


1. Values are generated with $R_L = 0\ \Omega$.
 In case of repetitive pulses, T_{jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

4 Package and PCB thermal data

4.1 SO-16L thermal data

Figure 21. SO-16L PC board⁽¹⁾



1. Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area = 41 mm x 48 mm, PCB thickness = 2 mm, Cu thickness = 35 μ m, Copper areas: 0.5 cm², 6 cm²).

Figure 22. $R_{thj-amb}$ vs PCB copper area in open box free air condition

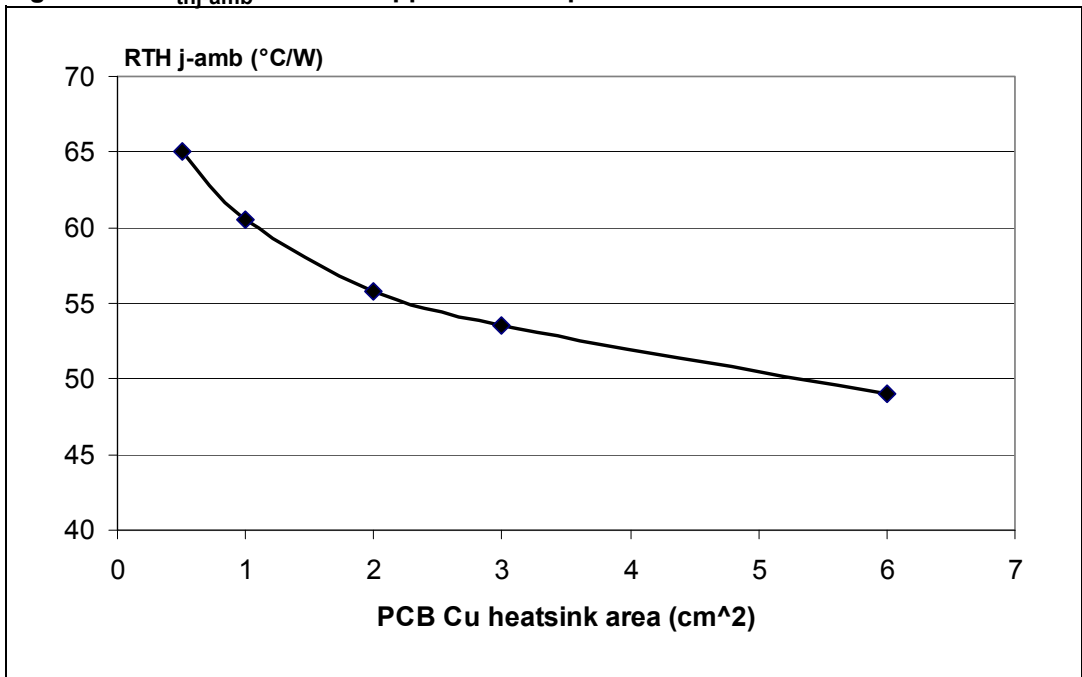
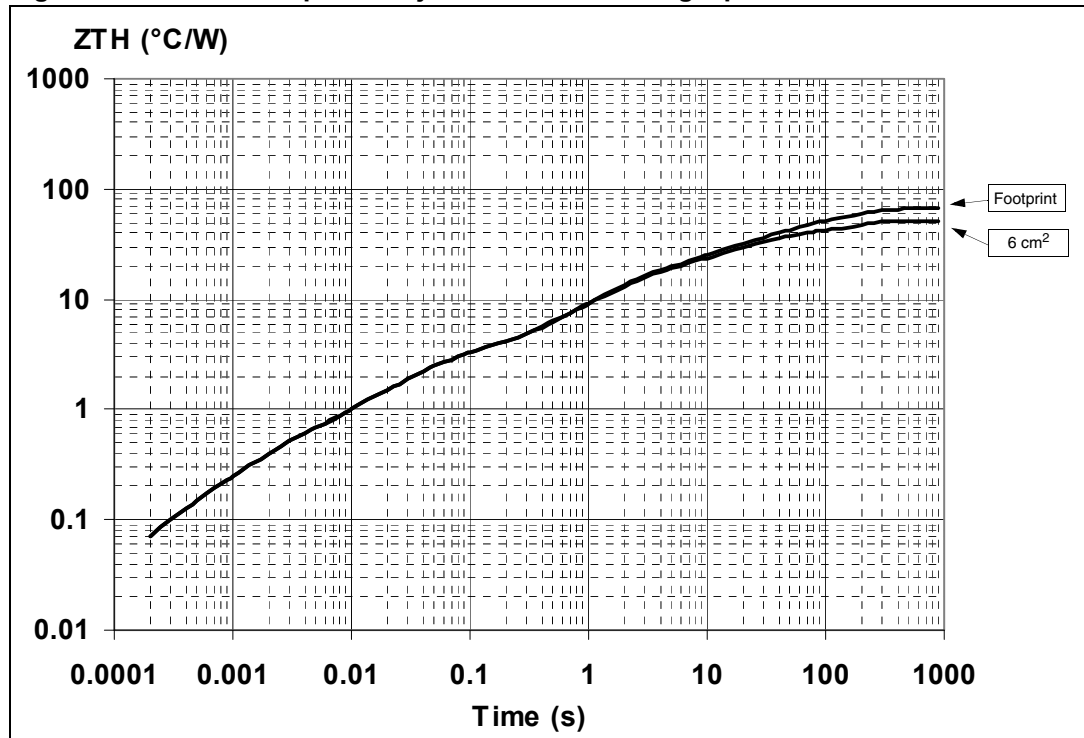


Figure 23. Thermal impedance junction ambient single pulse



Equation 1: pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p/T$

Figure 24. Thermal fitting model of a quad channel HSD in SO-16L

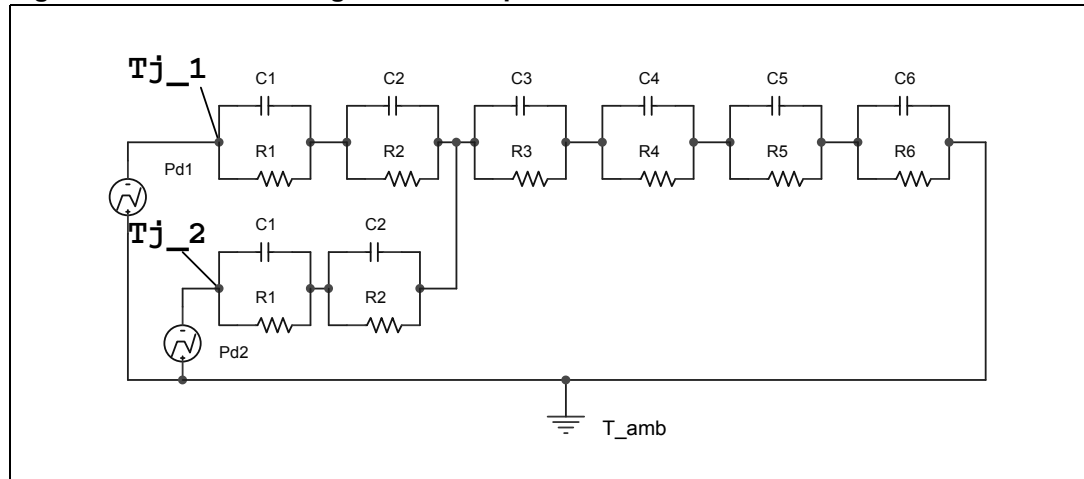


Table 13. Thermal parameters

Area / island (cm ²)	Footprint	6
R1 (°C/W)	0.05	
R2 (°C/W)	0.3	
R3 (°C/W)	2.2	
R4 (°C/W)	12	
R5 (°C/W)	15	
R6 (°C/W)	37	22
C1 (W.s/°C)	0.001	
C2 (W.s/°C)	5E-03	
C3 (W.s/°C)	0.02	
C4 (W.s/°C)	0.3	
C5 (W.s/°C)	1	
C6 (W.s/°C)	3	5

5 Package and packing information

5.1 ECOPACK[®] packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com.

ECOPACK[®] is an ST trademark.

Figure 25. SO-16L package dimensions

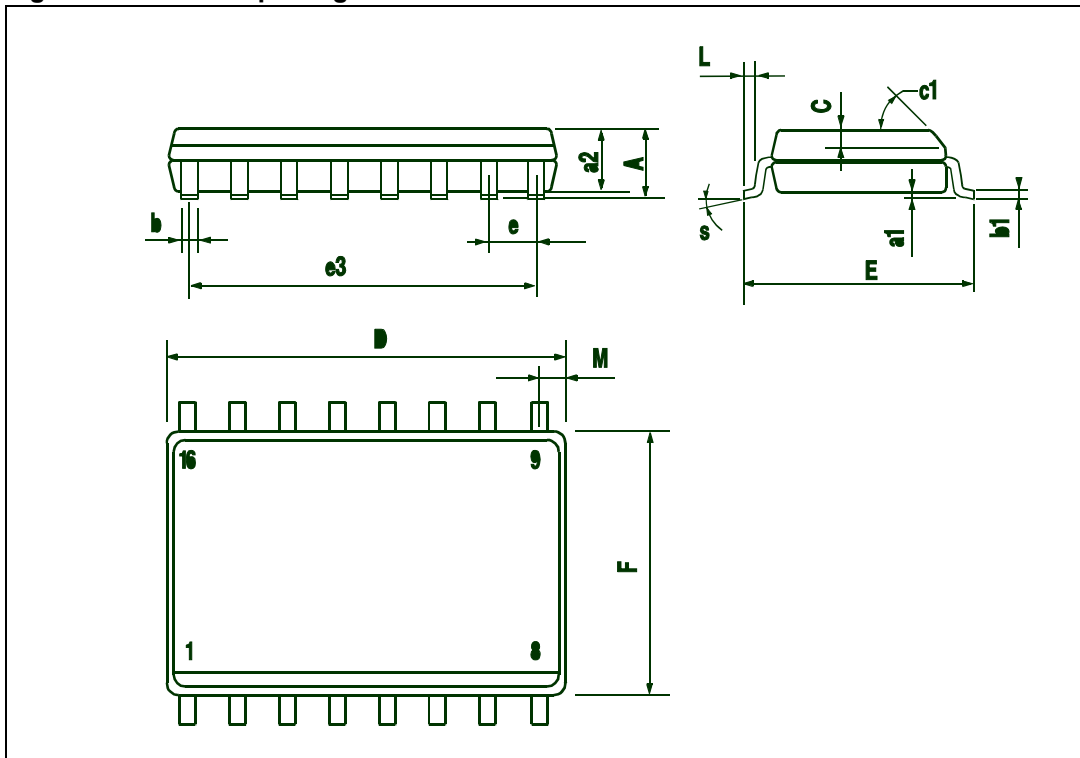


Table 14. SO-16L mechanical data

DIM.	mm.		
	Min.	Typ.	Max.
A			2.65
a1	0.1		0.2
a2			2.45
b	0.35		0.49
b1	0.23		0.32
C		0.5	
c1	45° (typ.)		
D	10.1		10.5
E	10.0		10.65
e		1.27	
e3		8.89	
F	7.4		7.6
L	0.5		1.27
M			0.75
S	8° (max.)		

5.2 SO-16L packing information

Figure 26. SO-16L tube shipment (no suffix)

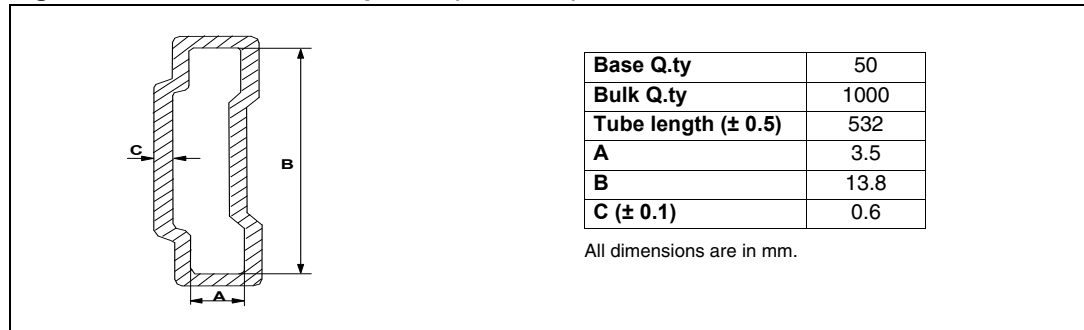
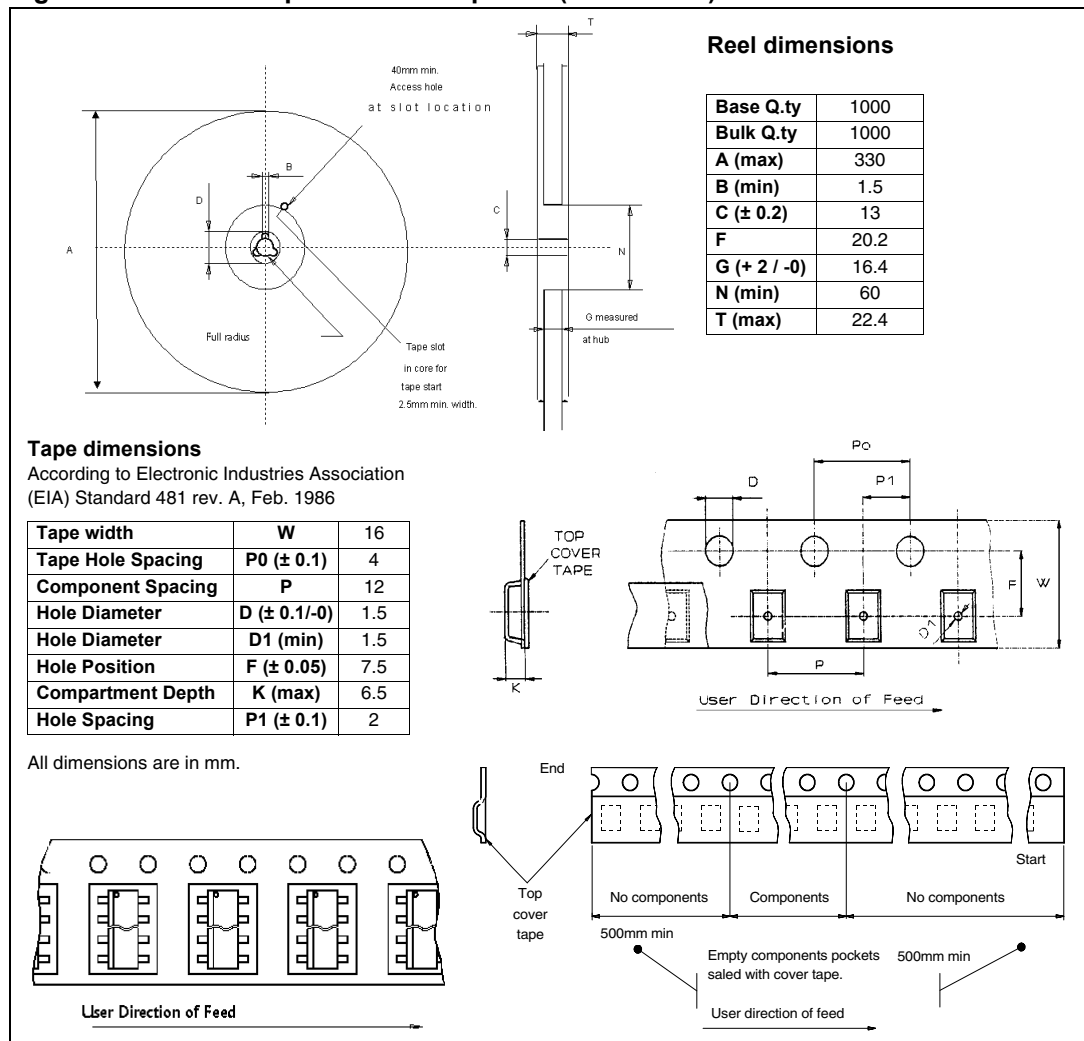


Figure 27. SO-16L tape and reel shipment (suffix "TR")



6 Revision history

Table 15. Document revision history

Date	Revision	Changes
20-Jul-2010	1	Initial release.
19-Sep-2013	2	Updated Disclaimer